

Title (en)
PASSIVATION METHOD

Title (de)
PASSIVIERUNGSVERFAHREN

Title (fr)
PROCEDE DE PASSIVATION

Publication
EP 4441799 A1 20241009 (FR)

Application
EP 22821485 A 20221122

Priority
• FR 2112689 A 20211129
• EP 2022082868 W 20221122

Abstract (en)
[origin: WO2023094403A1] Passivation method comprising the successive steps of: a) providing a structure comprising: - a substrate (1) based on crystalline silicon and having opposing first and second surfaces (10, 11); - first and second oxide films (2, 3); b) applying ultraviolet radiation to the structure, in an ozone atmosphere, so that the first oxide film (2') has: - a thickness strictly greater than that of the second oxide film (3), and/or - a composition closer to the stoichiometric compound; c) forming first and second layers of polysilicon (4, 5) on the first and second oxide films (2', 3), respectively, and comprising phosphorus atoms and boron atoms, respectively ; d) applying a heat treatment at a temperature greater than or equal to the electrical activation temperature of the boron atoms so as to electrically activate the phosphorus atoms and boron atoms at the same time.

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